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March 2014



FAN7387 Self-Oscillated, High-Voltage Gate Driver

Features

- Internal Clock Using RCT
- External Sync Function Using RCT
- Dead Time Control Using Resistor
- Shut Down (Disable Mode)
- Internal Shunt Regulator
- UVLO Function, High and Low Side

Applications

- Half-Bridge Inverter
- SMPS
- Ballast Solution for High-Intensity Discharge (HID) Lamp
- Ballast for Fluorescent Lamp

Description

The FAN7387 is a simple control IC for common halfbridge inverters, SMPS, and ballast for fluorescent and HID lamps. The FAN7387 has an oscillating circuit using an external resistor and capacitor.

The frequency variation is very stable across a wide temperature range. The FAN7387 has an external pin for dead-time control and shutdown. Using this resistor, the designer can choose the optimum dead time to reduce power loss on switching devices, such as transistors and MOSFETs.

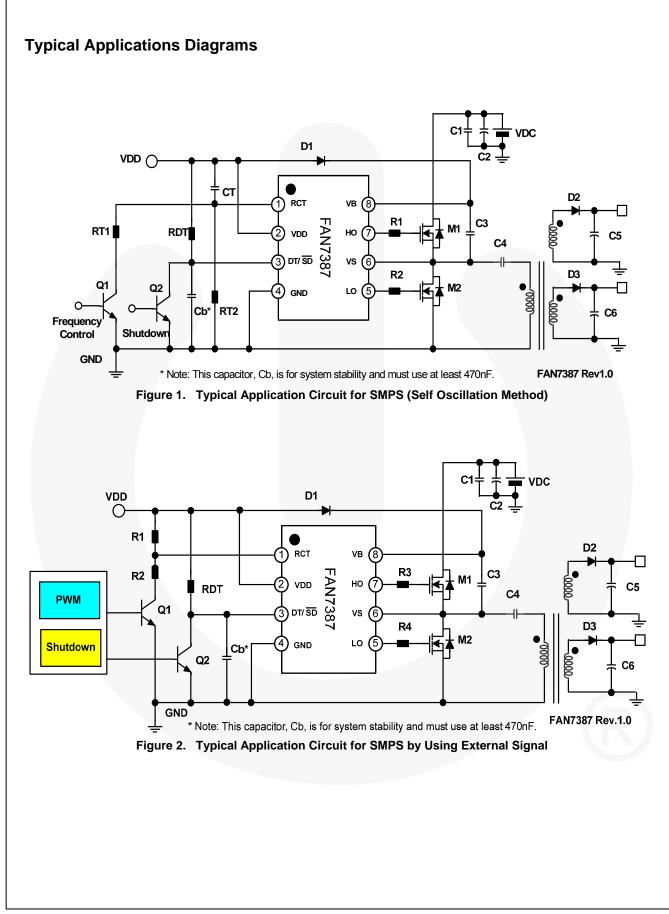


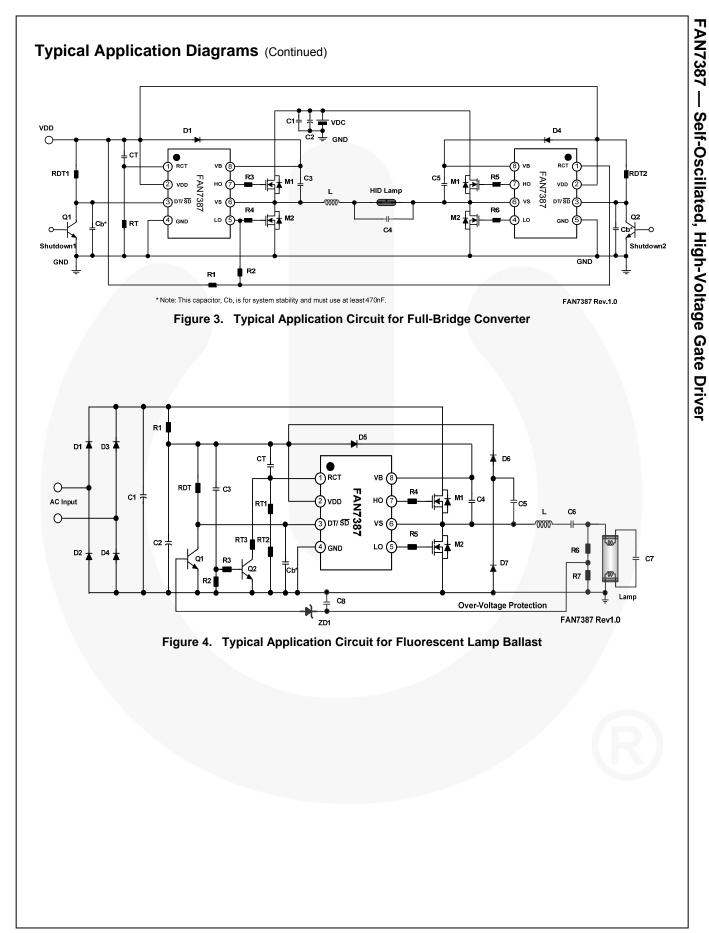
Ordering Information

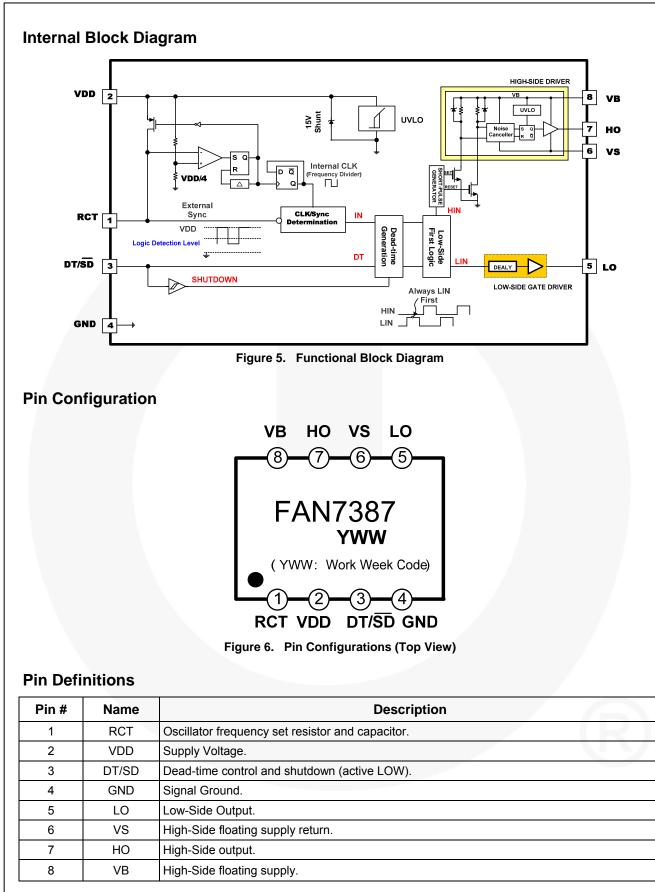
Part Number	Package	Operating Temperature	Packing Method
FAN7387MX ⁽¹⁾	8-SOP	-40 to +125°C	Tape & Reel

Note:

1. These device passed wave soldering test by JESD22A-111.







Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A=25$ °C unless otherwise specified.

Symbol	Parameter	Min.	Тур.	Max.	Unit
V _B	High-Side Floating Supply Voltage	-0.3		625.0	V
Vs	High-Side Offset Voltage	-0.3		600.0	V
V _{RCT}	RCT Pins Input Voltage			V _{CL}	V
I _{CL}	Clamping current level ⁽²⁾			25	mA
dV _S /dt	Allowable Offset Voltage Slew Rate		50		V/ns
T _A	Operating Temperature Range	-40		+125	°C
T _{STG}	Storage Temperature Range	-65		+150	°C
PD	Power Dissipation		0.625		W
Θ_{JA}	Thermal Resistance (Junction-to-Air)		200		°C/W

Note:

2. Do not supply a low-impedance voltage source to the internal clamping Zener diode between the GND and the VDD pin of this device.

Recommended Operating Ratings

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Min.	Max.	Unit.
V _B	High-Side Floating Supply Voltage	V _s +11	V _S +14	V
Vs	High-Side Offset Voltage	6-V _{DD}	600	V
V _{DD}	Low-Side Supply Voltage	11	14	V
V _{HO}	High-Side (HO) Output Voltage	GND	V _{DD}	V
V _{LO}	Low-Side (LO) Output Voltage	GND	V _{DD}	V
V _{IH}	Logic "1" Input Voltage of RCT	(3/4 V _{DD})+1		V
V _{IL}	Logic "0" Input Voltage of RCT		(3/5 V _{DD})-1	V
R _T	Timing Resistor Value of RCT	2		kΩ
CT	Timing Capacitor Value of RCT	100		pF
T _A	Ambient Temperature	-40	+125	°C

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Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Low-Sid	e Supply Characteristics (V _{DD})					
$VDD_{UV^{+}}$	V _{DD} Supply Under-Voltage Positive-Going Threshold	V _{DD} Increasing	9.50	11.00	12.50	V
VDD _{UV-}	V _{DD} Supply Under-Voltage Negative-Going Threshold	V _{DD} Decreasing	7.5	9.0	10.5	V
VDD_{UVH}	V _{DD} Supply Under-Voltage Lockout Hysteresis			2		V
V _{CL}	Supply Camping Voltage	I _{DD} =10 mA	14.8	15.4		V
I _{QDD}	Low-Side Quiescent Supply Current	R _{DT} =100 kΩ		220	500	μA
I _{ST}	Startup Supply Current	V _{DD} =9 V		50	130	μA
I _{LK}	Offset Supply Leakage Current	V _B =V _S =600 V			10	μA
I _{PDD}	Low-Side Dynamic Operating Supply Current			0.8		mA
High-Sic	de Supply Characteristics (V _B -V _S)					
VBS _{UV+}	V _{BS} Supply Under-Voltage Negative-Going Threshold	V _B -V _S Increasing	7.7	9.2	10.7	V
VBS _{UV-}	V _{BS} Supply Under-Voltage Negative-Going Threshold	V _B -V _S Decreasing	7.1	8.6	10.1	V
VBS _{UVH}	V _{BS} Supply Under-Voltage Lockout Hysteresis			0.6		V
I _{QBS}	High-Side Quiescent Supply Current			50	130	μA
I _{PBS}	High-Side Dynamic Operating Supply Current			400	800	μA
Oscillate	or Characteristics					
f _{osc1}	Oscillation Frequency 1	R _T =50 kΩ, C _T =330 pF	18	20	22	kHz
f _{osc2}	Oscillation Frequency 2	$R_T=1 k\Omega$, $C_T=1 nF$	210	250	290	kHz
D	Duty Cycle	Running Mode	47.5	49.0		%
V _{RCT+}	Upper Threshold Voltage of RCT	Running Mode		V_{DD}		V
V _{RCT-}	Lower Threshold Voltage of RCT	Running Mode		V _{DD} /4		V
V _{IH}	Logic "1" Input Voltage of RCT	Running Mode		3/4 V _{DD}		V
V _{IL}	Logic "0" Input Voltage of RCT	Running Mode			3/5 V _{DD}	V
t _D	Dead-Time	R _{DT} =100 kΩ	500	600	700	ns
t _{DMIN}	Minimum Dead-Time	V _{DT/SD} =V _{DD}	300	400	500	ns
Output (Characteristics					\sim
I _{O+}	Output High, Short-Circuit Pulse Current ⁽³⁾	PW≤10 µs		350		mA
I _{O-}	Output Low, Short-Circuit Pulse Current ⁽³⁾	PW≤10 µs		650		mA
Vs	Allowable Negative V_S Pin voltage for Input Signal (V_{RCT}) Propagation to HO			-9.8	-7.0	V

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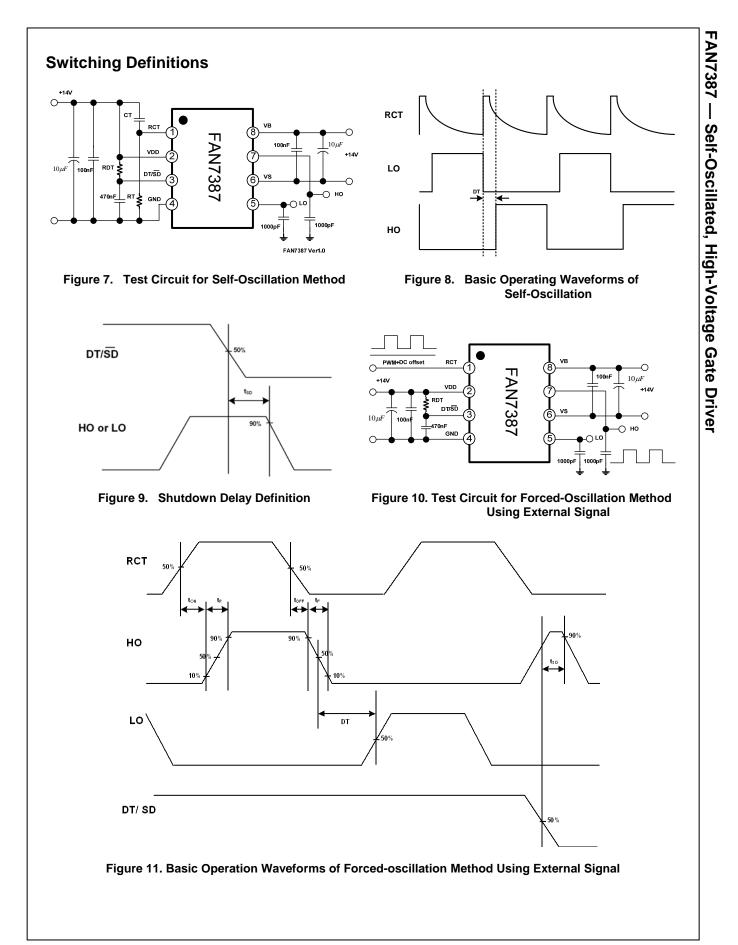
Electrical Characteristics (Continued)

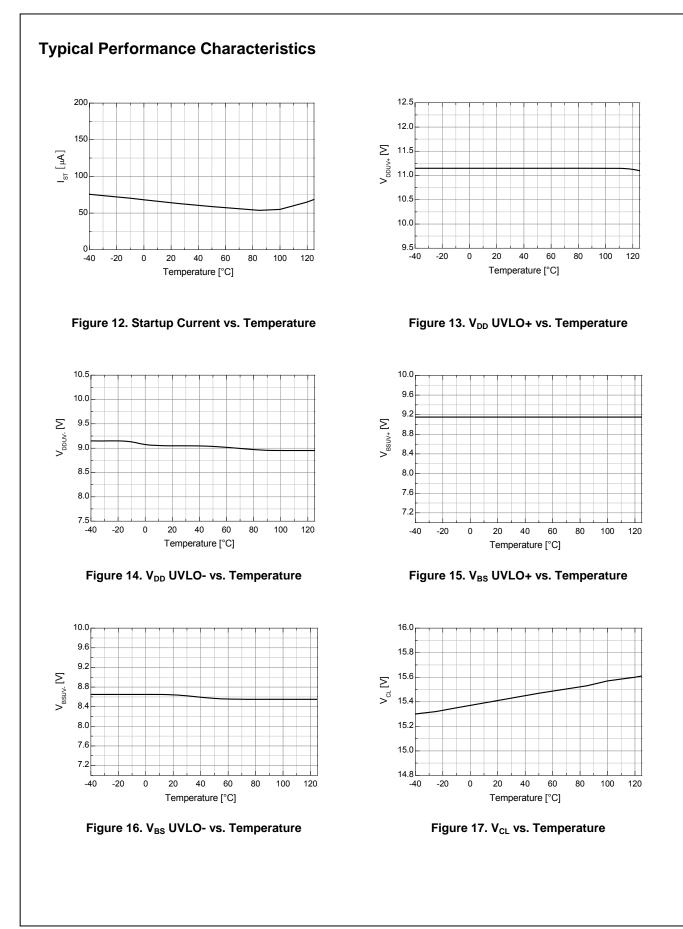
 $V_{BIAS} (V_{DD}, V_B - V_S) = 14.0 \text{ V}, \text{ } C_L = 1 \text{ nF}, \text{ } R_T = 50 \text{ } k\Omega \text{ and } C_T = 330 \text{ pF} \text{ and } T_A = 25^{\circ}C, \text{ } unless \text{ otherwise specified}.$

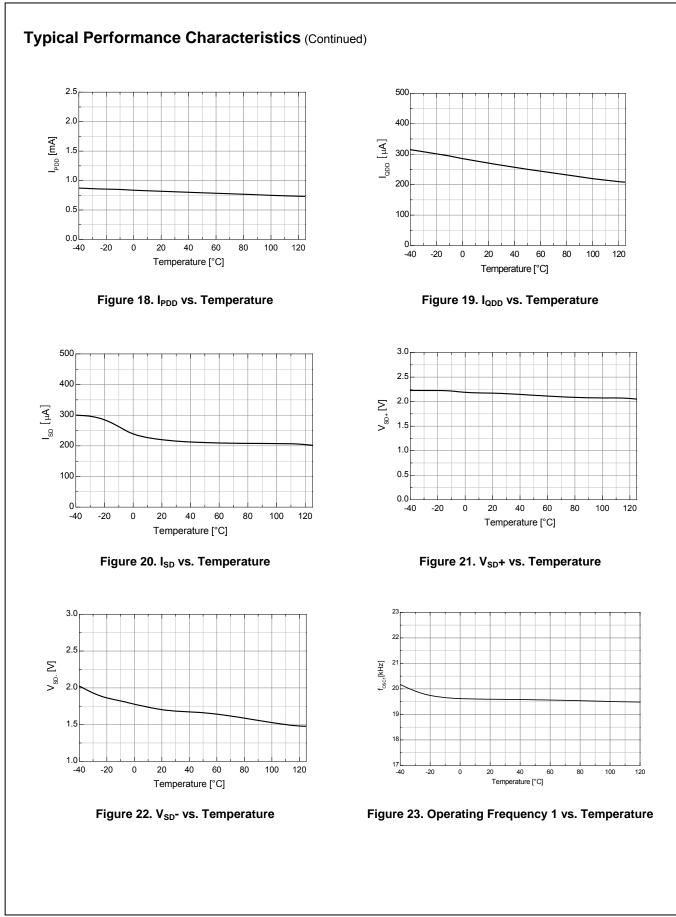
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Output Cha	aracteristics		·			
t _{on}	Turn-On Propagation Time	$V_{DD}=V_{BS}=14 V, V_{DT/SD}=V_{DD}, V_{RCT}=4 V \sim V_{DD}, f_{OSC}=20 \text{ kHz}$		550		ns
t _{OFF}	Turn-Off Propagation Time	$V_{DD}=V_{BS}=14 V, V_{DT/SD}=V_{DD}, V_{RCT}=4 V \sim V_{DD}, f_{OSC}=20 \text{ kHz}$		160		ns
t _R	Turn-On Rising Time	C _L =1000 pF		50	120	ns
t _F	Turn-Off Falling Time	C _L =1000 pF		30	70	ns
Protection	Characteristics					
/SD+	Shutdown "1" Input Voltage		2.7			V
/SD-	Shutdown "0" Input Voltage				1	V
I _{SD}	Shutdown Current	V _{DT/SD} =0 After Running Mode		250		μA
t _{SD}	Shutdown Propagation Delay			180		ns

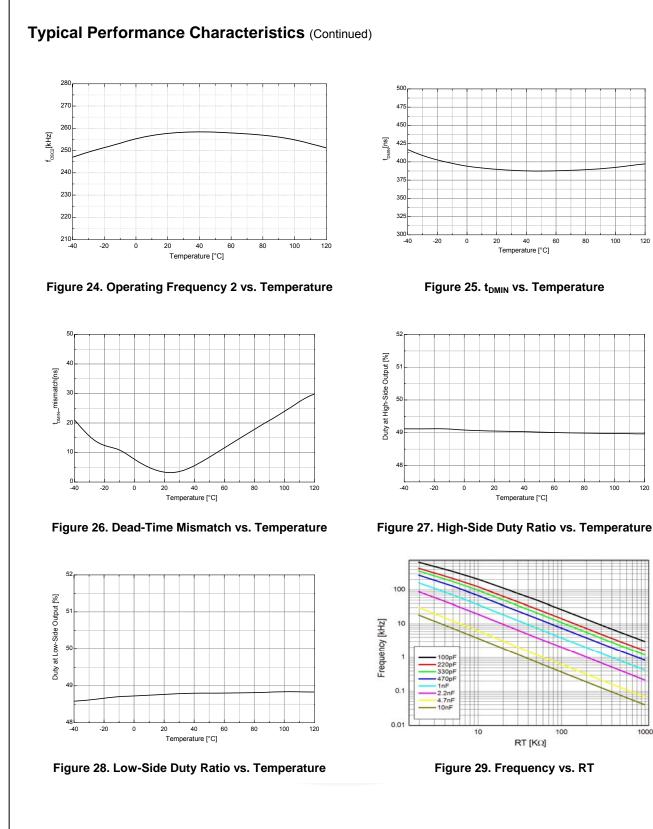
Note:

3. These parameters, although guaranteed, is not 100% tested in production.









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120

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Functional Description

1. Under-Voltage Lockout (UVLO) Function

FAN7387 has a UVLO circuit for a low-side and highside block. When V_{DD} reaches to the VDD_{UV}+, the UVLO circuit is released and the FAN7387 operates normally. At UVLO condition, the FAN7387 has a low supply current of less than 130 μ A. Once UVLO is released, FAN7387 operates normally until V_{DD} goes below VDD_{UV}-, the UVLO hysteresis.

FAN7387 also has a high-side gate driver. The supply for the high-side driver is applied between V_B and V_S. To prevent malfunction at low supply voltage between V_B and V_S, FAN7387 provides an additional UVLO circuit. If V_B-V_S is under VBS_{UV}+, the driver holds LOW state to turn off the high-side switch. Once the voltage of V_B-V_S is higher than VBS_{UVH}, after V_B-V_S exceeds VBS_{UV}-, the operation of driver resumes.

2. Oscillator

The running frequency is determined by an external timing resistor (R_T) and timing capacitor (C_T). The charge time of capacitor C_T from 1/4 V_{DD} to V_{DD} determines the running frequency of LO and HO gate driver output. Figure 30 shows connection configuration.

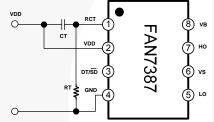


Figure 30. Typical Connection Method

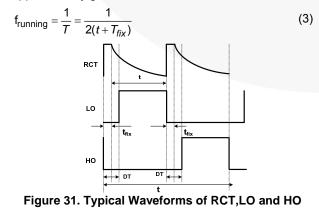
Figure 31 shows the typical waveforms of RCT, LO, and HO. From the circuit analysis, the discharging time of RCT, t, is given by Equation 1:

$$V_{\text{RCT}} = V_{DD} \times ln(\frac{-t}{R_t \times C_t})$$
(1)

Equation 1 enables calculation of discharging time, t, from V_{DD} to 1/4 V_{DD} by substituting $V_{RCT(t)}$ with 1/4 $V_{DD.}$

$$t = 1.38 \times R_t \times C_t \tag{2}$$

The running frequency of IC is determined by 1/T and is approximately given as:



where, t is the discharging time of the RCT voltage and $t_{\mbox{\scriptsize fix}}$ is constant value about 450 ns of IC.

3. Programming Dead-Time Control / Shutdown

A multi-function pin controls dead-time using an external resistor (R_{DT}) and protects abnormal condition using an external switch. This pin should be connected to an external capacitor to maintain stable operation.

If the voltage of DT/SD is decreased under 1 V by an external switch, such as the TR or MOSFET, the FAN7387 enters shutdown mode. In this mode, the FAN7387 doesn't have any output signal.

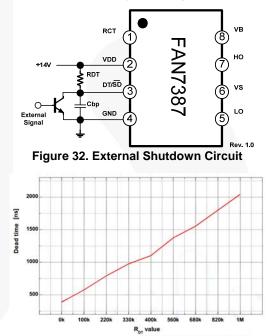


Figure 33. Adjustable Dead Time

4. Gate Driver Operation

The FAN7387 has a two operating modes. One is the self-oscillation mode by using external timing resistor (R_T) and external timing capacitor (C_T) and the other is the forced oscillation mode by external PWM signal comes from U-com and the other devices.

Figure 33 shows operation of the IC using an external PWM circuit with additional resistors (R1 and R2) for internal limitation of the IC. The input signal range from an external circuit must be within 3/5 V_{DD} and 3/4 V_{DD} . The external signal produces the HO and LO output and HO signal is in-phase with the external input signal.

